REVISION HISTORY

Revision	Description	Issue Date
Rev. 0.1	Initial Issue	Aug.20.2008
Rev. 0.2	Revised **FEATURES** & **ORDERING INFORMATION** **Lead free and green package available** to **Green package available** Added packing type in **ORDERING INFORMATION** Deleted T_{SOLDER} in **ABSOLUTE MAXIMUN RATINGS**	May.20.2009
Rev. 0.3	Revised **ORDERING INFORMATION** in page 11	Aug.30.2010
Rev. 1.0	Correct typo error on the column “UB#”, “LB#” of truth table for row “Byte Read” “Byte Write” and “Output Disable” at page 4: “X” revised to be “L”	Jul.08.2013
Rev. 1.1	Deleted **WRITE CYCLE** Notes : 1.WE#,CE#, LB#, UB# must be high or CE2 must be low during all address transitions. in page 8 Deleted E grade in **ABSOLUTE MAXIMUN RATINGS** Revised **ORDERING INFORMATION** in page 11	Jun.29.2016
Rev. 1.2	Added Power Type in **ORDERING INFORMATION** Revised **PIN DESCRIPTION** in page 2 Revised Head Title as “**16M Bits (2Mx8 / 1Mx16 Switchable) LOW POWER CMOS SRAM**”	Dec.06.2016
Rev. 1.3	Added **TRUTH TABLE** Notes: 2. The BYTE# pin has to be tied to V_{CC} to use the device as a 1M x 16 SRAM, and to be tied to V_{SS} as a 2M x 8 SRAM. In the 2M x 8 configuration, Pin 45 is A-1, and both UB# and LB# are tied to V_{SS}, while DQ8 to DQ14 pins are not used.	May.22.2017

16M Bits (2Mx8 / 1Mx16 Switchable) LOW POWER CMOS SRAM

FEATURES

- Fast access time : 55/70ns
- Low power consumption:
  Operating current : 45/30mA (TYP.)
  Standby current : 10μA (TYP.) LL-version
- Single 2.7V ~ 3.6V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data byte control :
  (i) BYTE# fixed to V_{CC}
  LB# controlled DQ0 ~ DQ7
  UB# controlled DQ8 ~ DQ15
  (ii) BYTE# fixed to V_{SS}
  DQ15 used as address pin, while
  DQ8~DQ14 pins not used
- Data retention voltage : 1.2V (MIN.)
- **Green package available**
- Package : 48-pin 12mm x 20mm TSOP I

GENERAL DESCRIPTION

The LY62L102616 is a 16,777,216-bit low power CMOS static random access memory organized as 1,048,576 words by 16 bits or 2,097,152 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

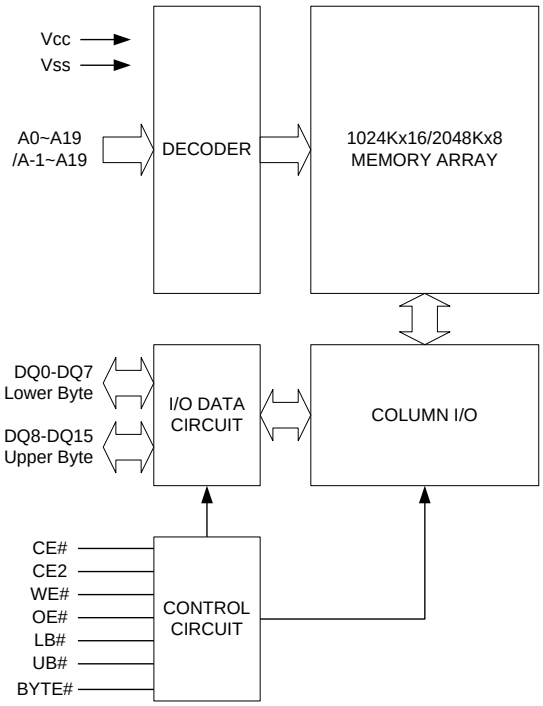
The LY62L102616 is well designed for low power application, and particularly well suited for battery back-up nonvolatile memory application.

The LY62L102616 operates from a single power supply of 2.7V ~ 3.6V and all inputs and outputs are fully TTL compatible

PRODUCT FAMILY

Product Family	Operating Temperature	V_{CC} Range	Speed	Power Dissipation	
				Standby(I_{SB1},TYP.)	Operating(I_{CC},TYP.)
LY62L102616	0 ~ 70℃	2.7 ~ 3.6V	55/70ns	10μA(LL)	45/30mA
LY62L102616(I)	-40 ~ 85℃	2.7 ~ 3.6V	55/70ns	10μA(LL)	45/30mA

FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A19	Address Inputs(word mode)
A-1 - A19	Address Inputs(byte mode)
DQ0 - DQ15	Data Inputs/Outputs
CE#, CE2	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
LB#	Lower Byte Control
UB#	Upper Byte Control
BYTE#	Byte Enable
V_{CC}	Power Supply
V_{SS}	Ground
NC	No Connection

PIN CONFIGURATION

TSOP I

ABSOLUTE MAXIMUN RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on V_{CC} relative to V_{SS}	V_{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to V_{SS}	V_{T2}	-0.5 to V_{CC}+0.5	V
Operating Temperature	T_A	0 to 70(C grade)	℃
		-40 to 85(I grade)	
Storage Temperature	T_{STG}	-65 to 150	℃
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA

*Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	CE2	BYTE#	OE#	WE#	LB#	UB#	I/O OPERATION			SUPPLY CURRENT
								DQ0-DQ7	DQ8-DQ14	DQ15	
Standby	H	X	X	X	X	X	X	High-Z	High-Z	High-Z	I_{SB},I_{SB1}
	X	L	X	X	X	X	X	High-Z	High-Z	High-Z	
	X	X	H	X	X	H	H	High-Z	High-Z	High-Z	
Output Disable	L	H	H	H	H	L	X	High-Z	High-Z	High-Z	I_{CC},I_{CC1}
	L	H	H	H	H	X	L	High-Z	High-Z	High-Z	
	L	H	L	H	H	L	L	High-Z	High-Z	A-1	
Read	L	H	H	L	H	L	H	D_{OUT}	High-Z	High-Z	I_{CC},I_{CC1}
	L	H	H	L	H	H	L	High-Z	D_{OUT}	D_{OUT}	
	L	H	H	L	H	L	L	D_{OUT}	D_{OUT}	D_{OUT}	
Write	L	H	H	X	L	L	H	D_{IN}	High-Z	High-Z	I_{CC},I_{CC1}
	L	H	H	X	L	H	L	High-Z	D_{IN}	D_{IN}	
	L	H	H	X	L	L	L	D_{IN}	D_{IN}	D_{IN}	
Byte# Read	L	H	L	L	H	L	L	D_{OUT}	High-Z	A-1	I_{CC},I_{CC1}
Byte # Write	L	H	L	X	L	L	L	D_{IN}	High-Z	A-1	I_{CC},I_{CC1}

Notes:
1. H = V_{IH}, L = V_{IL}, X = Don't care.
2. The BYTE# pin has to be tied to V_{CC} to use the device as a 1M x 16 SRAM, and to be tied to V_{SS} as a 2M x 8 SRAM. In the 2M x 8 configuration, Pin 45 is A-1, and both UB# and LB# are tied to V_{SS}, while DQ8 to DQ14 pins are not used.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP. *4	MAX.	UNIT
Supply Voltage	V_{CC}			2.7	3.0	3.6	V
Input High Voltage	V_{IH} *1			2.2	-	V_{CC}+0.3	V
Input Low Voltage	V_{IL} *2			- 0.2	-	0.6	V
Input Leakage Current	I_{LI}	$V_{CC} \geqq V_{IN} \geqq V_{SS}$		- 1	-	1	µA
Output Leakage Current	I_{LO}	$V_{CC} \geqq V_{OUT} \geqq V_{SS}$ Output Disabled		- 1	-	1	µA
Output High Voltage	V_{OH}	I_{OH} = -1mA		2.2	2.7	-	V
Output Low Voltage	V_{OL}	I_{OL} = 2mA		-	-	0.4	V
Average Operating Power supply Current	I_{CC}	Cycle time = MIN. CE# = V_{IL} and CE2 = V_{IH} $I_{I/O}$ = 0mA Other pins at V_{IL} or V_{IH}	- 55	-	45	60	mA
			- 70	-	30	45	mA
	I_{CC1}	Cycle time = 1µs CE#≦ 0.2V and CE2≧ V_{CC}-0.2V $I_{I/O}$ = 0mA Other pins at 0.2V or V_{CC}-0.2V		-	8	16	mA
Standby Power Supply Current	I_{SB}	CE# = V_{IH} or CE2 = V_{IL} Other pins at V_{IL} or V_{IH}		-	0.3	2	mA
	I_{SB1}	CE# ≧ V_{CC}-0.2V or CE2≦ 0.2V Other pins at 0.2V or V_{CC}-0.2V	LL	-	10	60	µA
			LLI	-	10	100	µA

Notes:
1. V_{IH}(max) = V_{CC} + 2.0V for pulse width less than 6ns.
2. V_{IL}(min) = V_{SS} - 2.0V for pulse width less than 6ns.
3. Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.
4. Typical values are included for reference only and are not guaranteed or tested.
   Typical valued are measured at V_{CC} = V_{CC}(TYP.) and T_A = 25℃

CAPACITANCE (T_A = 25℃, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0.2V to V_{CC} - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	C_L = 30pF + 1TTL, I_{OH}/I_{OL} = -1mA/2mA

AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

PARAMETER	SYM.	LY62L102616-55		LY62L102616-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	55	-	70	-	ns
Address Access Time	t_{AA}	-	55	-	70	ns
Chip Enable Access Time	t_{ACE}	-	55	-	70	ns
Output Enable Access Time	t_{OE}	-	30	-	35	ns
Chip Enable to Output in Low-Z	t_{CLZ}*	10	-	10	-	ns
Output Enable to Output in Low-Z	t_{OLZ}*	5	-	5	-	ns
Chip Disable to Output in High-Z	t_{CHZ}*	-	20	-	25	ns
Output Disable to Output in High-Z	t_{OHZ}*	-	20	-	25	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	ns
LB#, UB# Access Time	t_{BA}	-	55	-	70	ns
LB#, UB# to High-Z Output	t_{BHZ}*	-	25	-	30	ns
LB#, UB# to Low-Z Output	t_{BLZ}*	10	-	10	-	ns

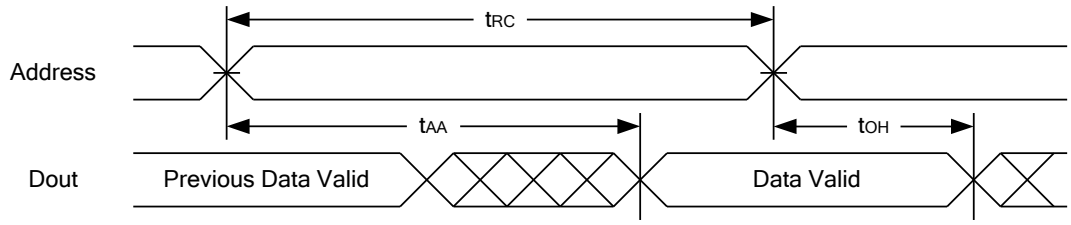
(2) WRITE CYCLE

PARAMETER	SYM.	LY62L102616-55		LY62L102616-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	55	-	70	-	ns
Address Valid to End of Write	t_{AW}	50	-	60	-	ns
Chip Enable to End of Write	t_{CW}	50	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	ns
Write Pulse Width	t_{WP}	45	-	55	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	25	-	30	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	ns
Output Active from End of Write	t_{OW}*	5	-	5	-	ns
Write to Output in High-Z	t_{WHZ}*	-	20	-	25	ns
LB#, UB# Valid to End of Write	t_{BW}	45	-	60	-	ns

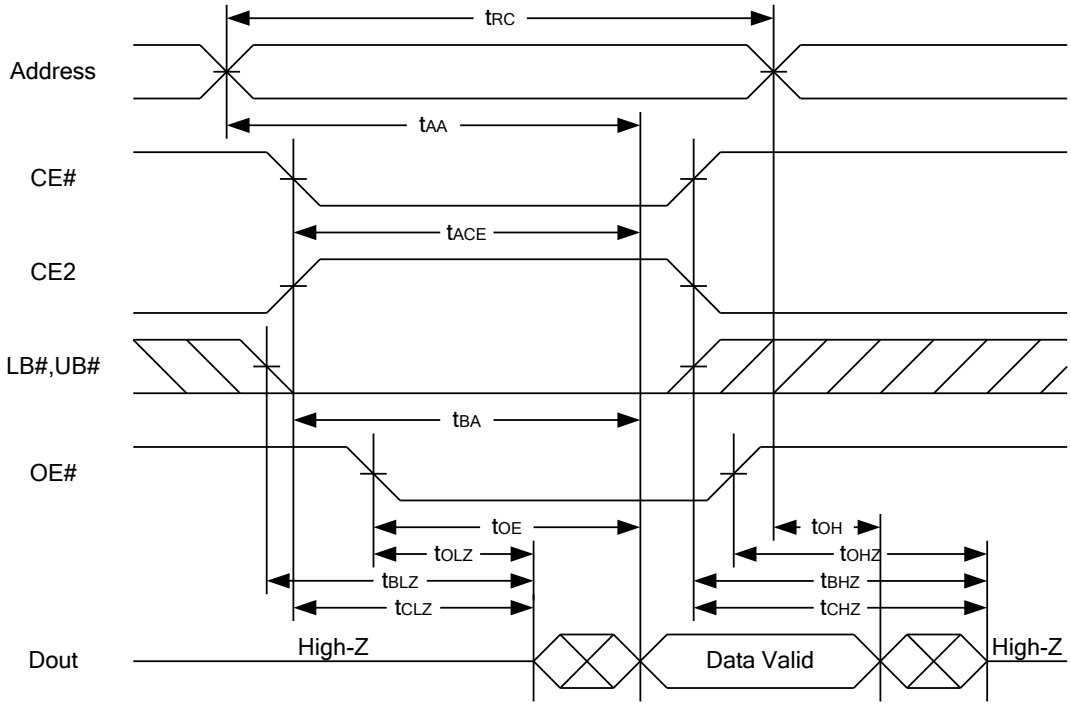
*These parameters are guaranteed by device characterization, but not production tested.

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)

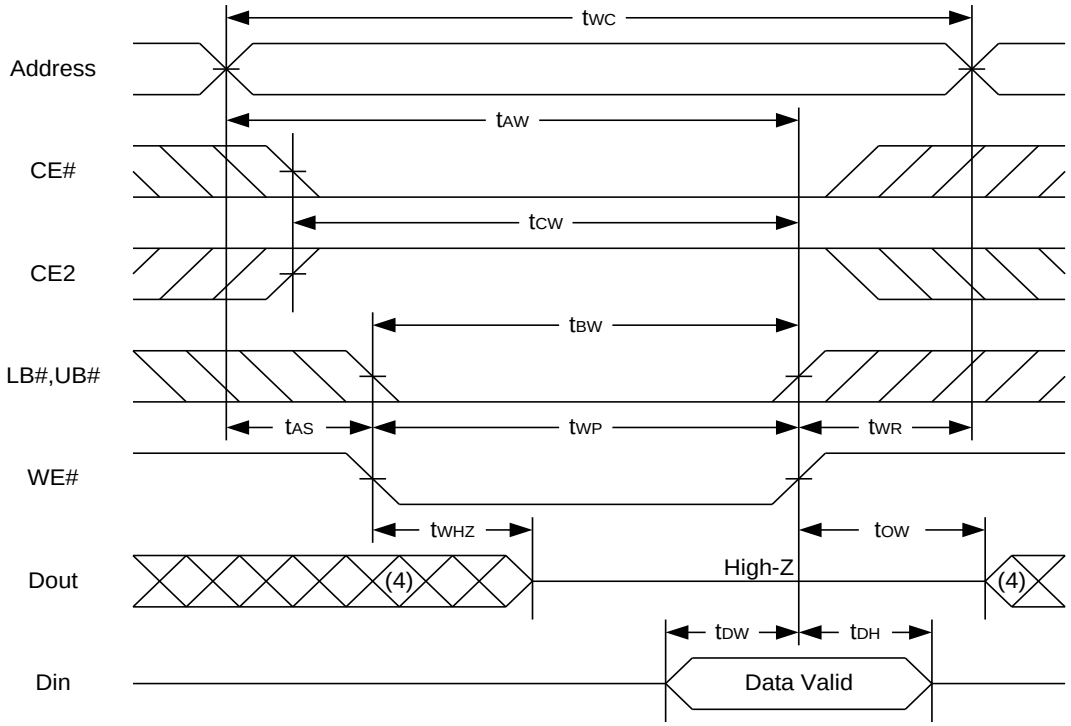


READ CYCLE 2 (CE# and CE2 and OE# Controlled) (1,3,4,5)

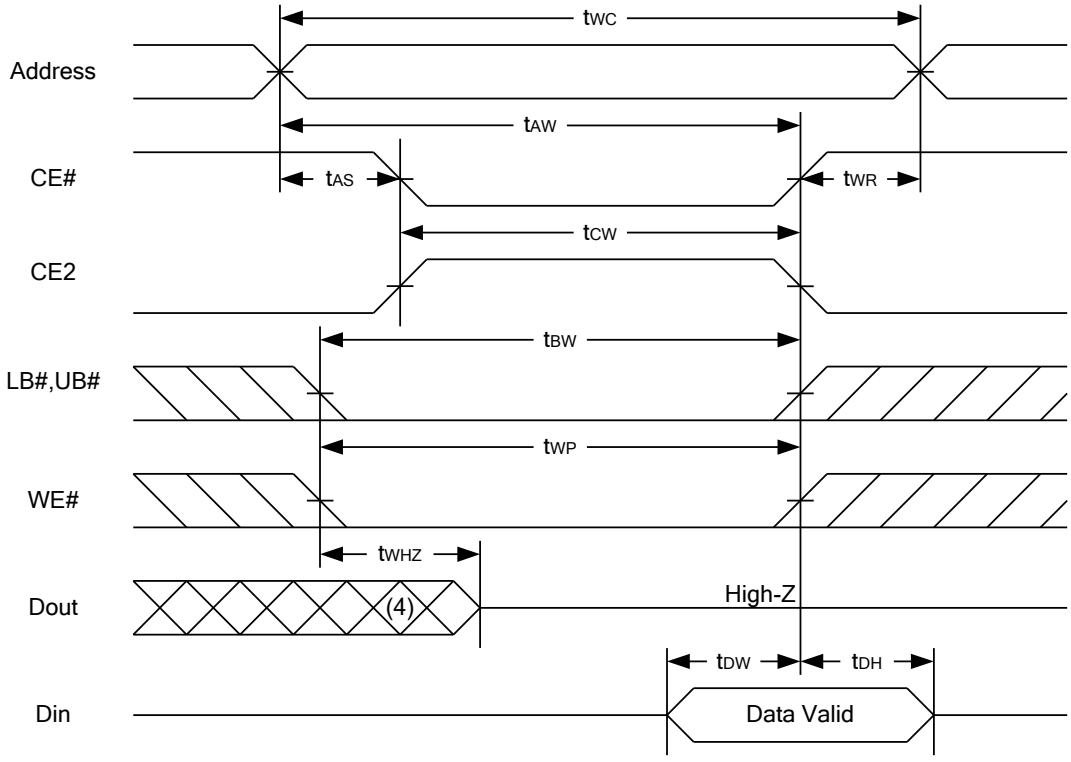


Notes :
1.WE# is high for read cycle.
2.Device is continuously selected OE# = low, CE# = low, CE2 = high, LB# or UB# = low.
3.Address must be valid prior to or coincident with CE# = low, CE2 = high, LB# or UB# = low transition; otherwise t_{AA} is the limiting parameter.
4.t_{CLZ}, t_{BLZ}, t_{OLZ}, t_{CHZ}, t_{BHZ} and t_{OHZ} are specified with C_L = 5pF. Transition is measured ±500mV from steady state.
5.At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{BHZ} is less than t_{BLZ}, t_{OHZ} is less than t_{OLZ}.

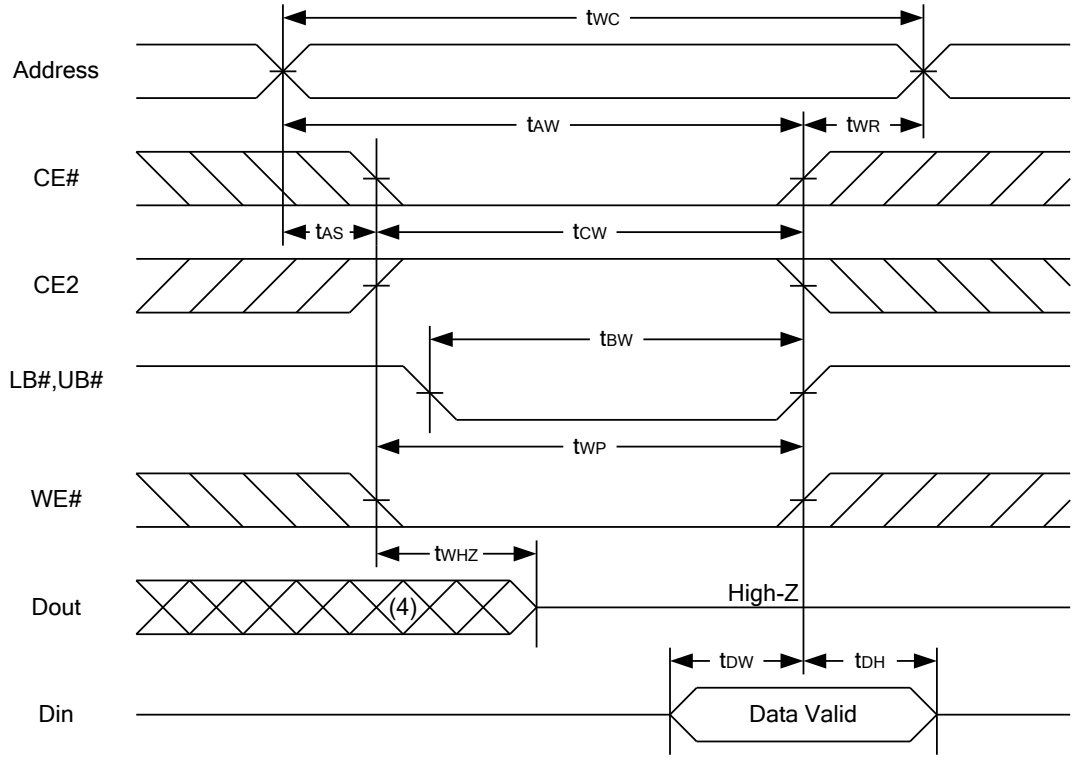
WRITE CYCLE 1 (WE# Controlled) (1,2,4,5)



WRITE CYCLE 2 (CE# and CE2 Controlled) (1,4,5)



WRITE CYCLE 3 (LB#,UB# Controlled) (1,4,5)



Notes :
1.A write occurs during the overlap of a low CE#, high CE2, low WE#, LB# or UB# = low.
2.During a WE# controlled write cycle with OE# low, t_{WP} must be greater than $t_{WHZ} + t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
3.During this period, I/O pins are in the output state, and input signals must not be applied.
4.If the CE#, LB#, UB# low transition and CE2 high transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
5.t_{OW} and t_{WHZ} are specified with C_L = 5pF. Transition is measured ±500mV from steady state.

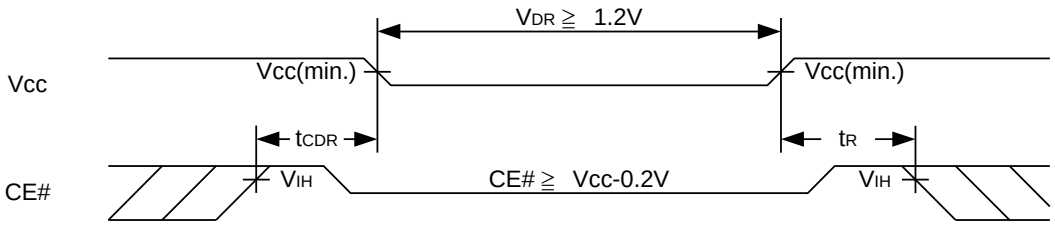
DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
V_{CC} for Data Retention	V_{DR}	CE#≧ V_{CC} - 0.2V or CE2≦ 0.2V		1.2	-	3.6	V
Data Retention Current	I_{DR}	V_{CC} = 1.2V CE# ≧ V_{CC}-0.2V or CE2≦ 0.2V other pins at 0.2V or V_{CC}-0.2V	LL	-	4	50	µA
			LLI	-	4	80	µA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)		0	-	-	ns
Recovery Time	t_R			t_{RC*}	-	-	ns

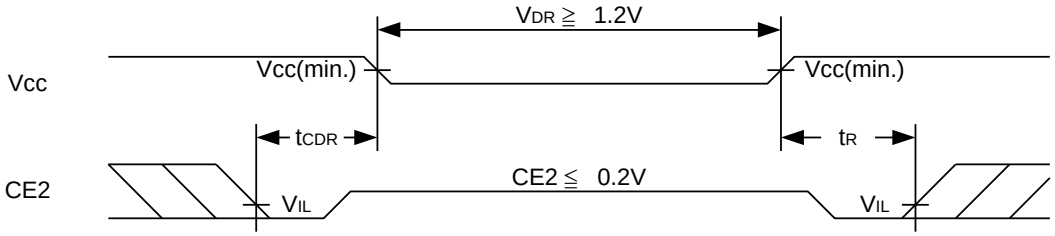
t_{RC*} = Read Cycle Time

DATA RETENTION WAVEFORM

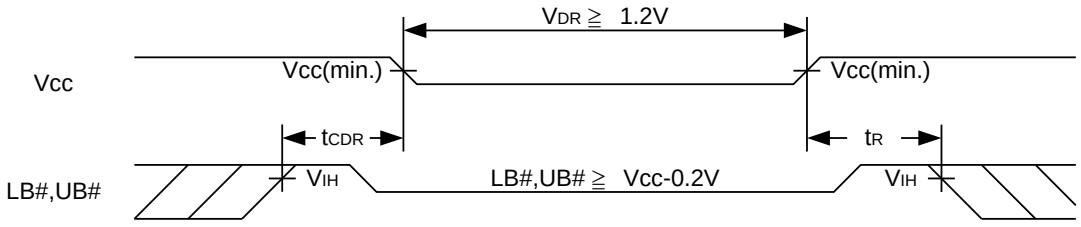
Low V_{CC} Data Retention Waveform (1) (CE# controlled)



Low V_{CC} Data Retention Waveform (2) (CE2 controlled)

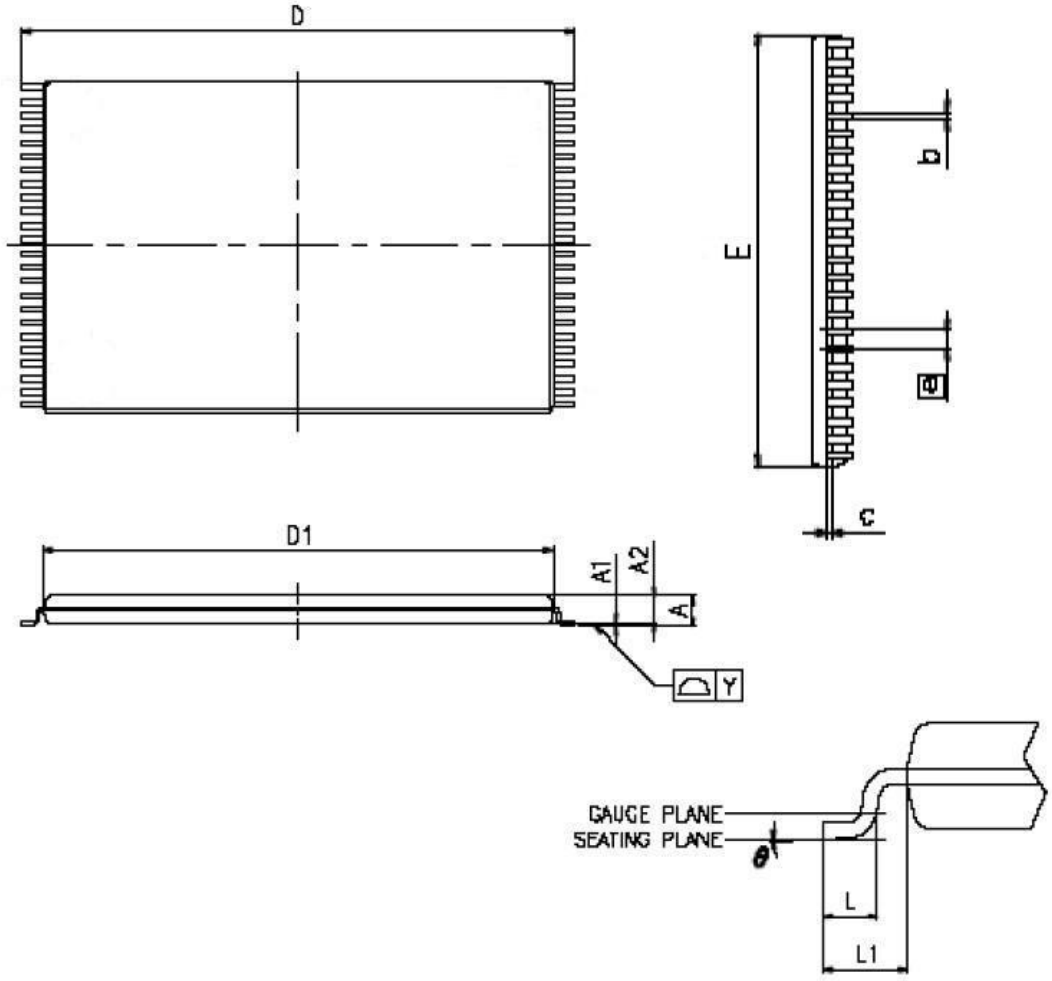


Low V_{CC} Data Retention Waveform (3) (LB#, UB# controlled)



PACKAGE OUTLINE DIMENSION

48-pin 12mm x 20mm TSOP I Package Outline Dimension



VARIATIONS (ALL DIMENSIONS SHOWN IN MM)

	SYMBOLS	MIN.	NOM.	MAX
	A	–	–	1.20
	A1	0.05	–	0.15
	A2	0.95	1.00	1.05
	b	0.17	0.22	0.27
	c	0.10	–	0.21
⚠	D	19.80	20.00	20.20
⚠	D1	18.30	18.40	18.50
⚠	E	11.90	12.00	12.10
	e	0.50 BASIC		
	L	0.50	0.60	0.70
⚠	L1	–	0.80	–
⚠	Y	–	–	0.10
⚠	θ	0°	–	5°

NOTES:
1 JEDEC OUTLINE : MO-142 DD
2.PROFILE TOLERANCE ZONES FOR D1 AND E DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTRUSION ON E IS 0.15mm PER SIDE AND ON D1 IS 0.25mm PER SIDE.
3.DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUN MATERIAL CONDITION DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.

ORDERING INFORMATION

Package Type	Access Time (Speed)(ns)	Power Type	Temperature Range(℃)	Packing Type	Lyontek Item No.
48-pin (12mm x 20mm) TSOP I	55	Ultra Low Power	0℃~70℃	Tray	LY62L102616LL-55LL
				Tape Reel	LY62L102616LL-55LLT
			-40℃~85℃	Tray	LY62L102616LL-55LLI
				Tape Reel	LY62L102616LL-55LLIT
	70	Ultra Low Power	0℃~70℃	Tray	LY62L102616LL-70LL
				Tape Reel	LY62L102616LL-70LLT
			-40℃~85℃	Tray	LY62L102616LL-70LLI
				Tape Reel	LY62L102616LL-70LLIT

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